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Kind regards,

Team Nexperia



PBHV9115TLH

150 V, 1 A PNP high-voltage low V_{CEsat} BISS transistor

16 January 2017

Product data sheet

1. General description

PNP high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8115TLH

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- Small SMD plastic package
- AEC-Q101 qualified

3. Applications

- Power management
- LCD backlighting
- LED driver for LED chain module
- Switch Mode Power Supply (SMPS)

4. Quick reference data

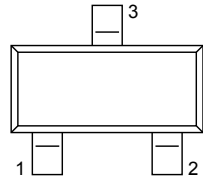
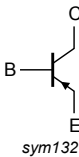
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-150	V
I _C	collector current		-	-	-1	A
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-2	A
h _{FE}	DC current gain	V _{CE} = -10 V; I _C = -50 mA; T _{amb} = 25 °C	70	-	300	



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base	 TO-236AB (SOT23)	 sym132
2	E	emitter		
3	C	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBHV9115TLH	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PBHV9115TLH	FC%

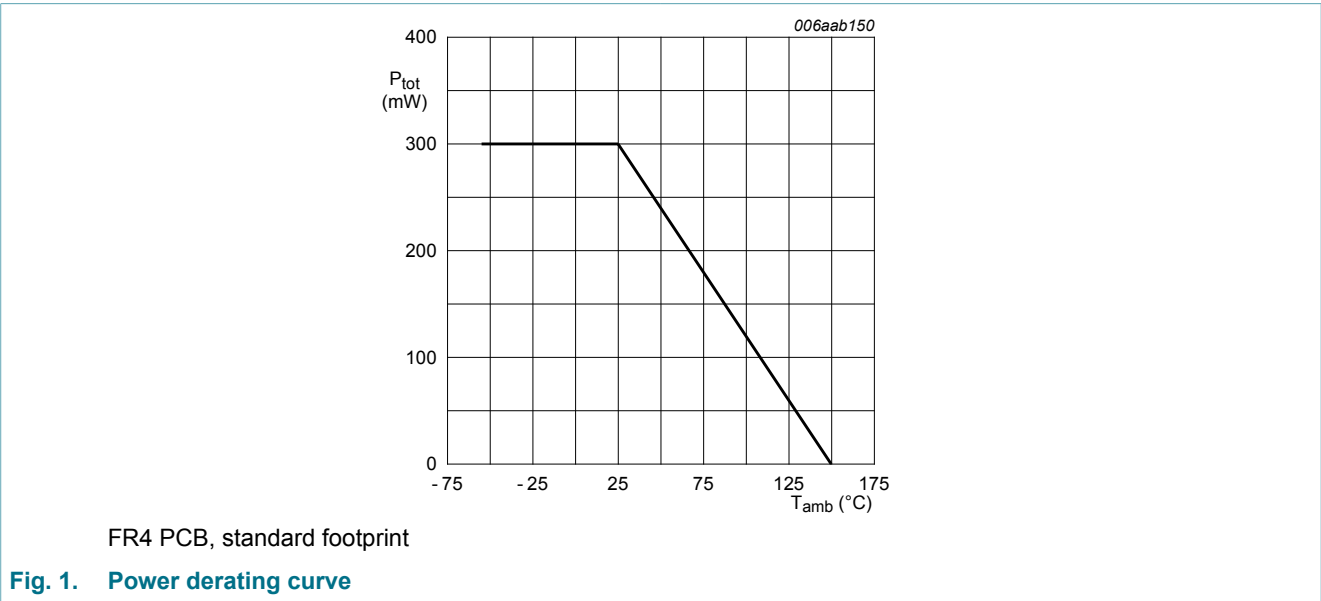
[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-200	V
V _{CEO}	collector-emitter voltage	open base		-	-150	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	-200	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-1	A
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-2	A
I _{BM}	peak base current			-	-400	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

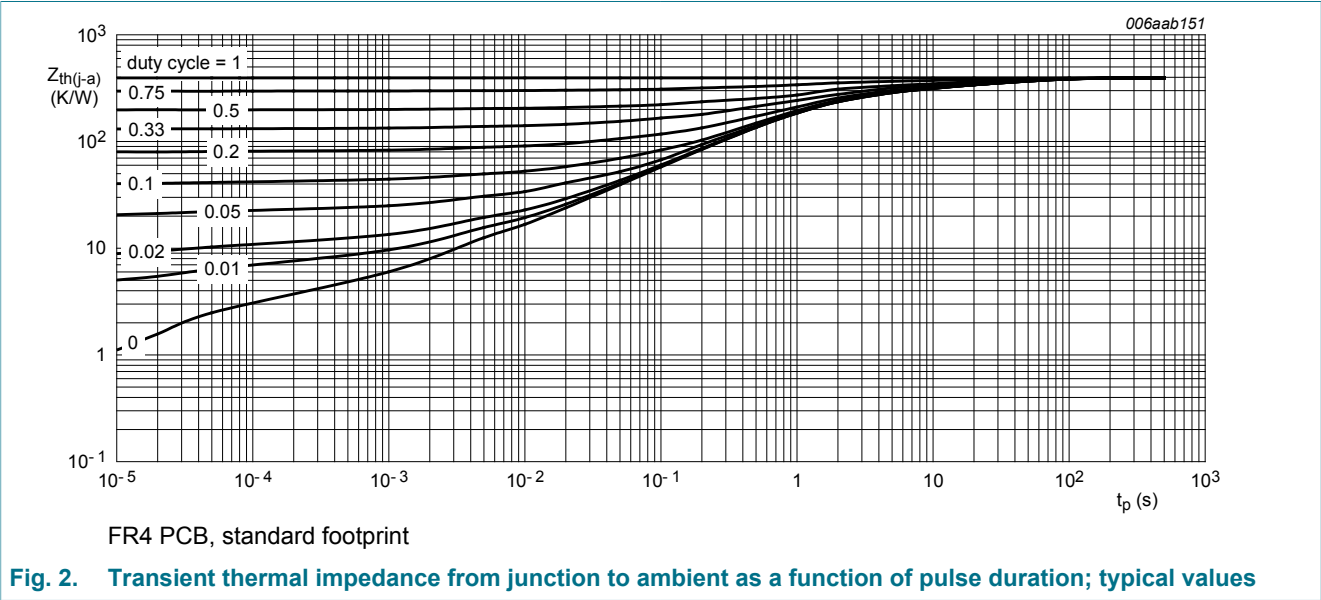


9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	70	K/W

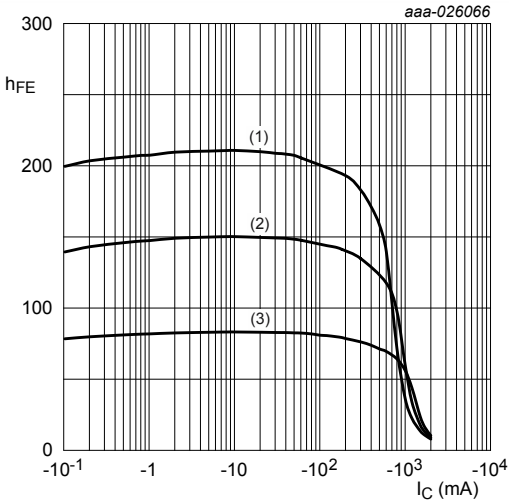
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



10. Characteristics

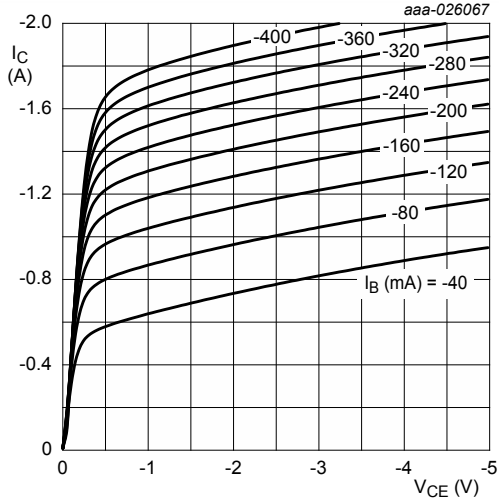
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = -120\text{ V}$; $I_E = 0\text{ A}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-100	nA
		$V_{CB} = -120\text{ V}$; $I_E = 0\text{ A}$; $T_j = 150\text{ }^{\circ}\text{C}$	-	-	-10	μA
I_{CES}	collector-emitter cut-off current	$V_{CE} = -120\text{ V}$; $V_{BE} = 0\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}$; $I_C = 0\text{ A}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-100	nA
h_{FE}	DC current gain	$V_{CE} = -10\text{ V}$; $I_C = -50\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	70	-	300	
		$V_{CE} = -10\text{ V}$; $I_C = -100\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	60	-	300	
		$V_{CE} = -10\text{ V}$; $I_C = -500\text{ mA}$; pulsed; $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	50	-	300	
		$V_{CE} = -10\text{ V}$; $I_C = -1\text{ A}$; pulsed; $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	10	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -100\text{ mA}$; $I_B = -10\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-120	mV
		$I_C = -100\text{ mA}$; $I_B = -20\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-100	mV
		$I_C = -500\text{ mA}$; $I_B = -100\text{ mA}$; pulsed; $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-300	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -1\text{ A}$; $I_B = -200\text{ mA}$; pulsed; $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-1.2	V
t_d	delay time	$V_{CC} = -6\text{ V}$; $I_C = -0.5\text{ A}$; $I_{Bon} = -0.1\text{ mA}$; $I_{Boff} = 0.1\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	10	-	ns
t_r	rise time		-	285	-	ns
t_{on}	turn-on time		-	295	-	ns
t_s	storage time		-	430	-	ns
t_f	fall time		-	300	-	ns
t_{off}	turn-off time		-	730	-	ns
f_T	transition frequency	$V_{CE} = -10\text{ V}$; $I_C = -10\text{ mA}$; $f = 100\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	55	-	MHz
C_c	collector capacitance	$V_{CB} = -20\text{ V}$; $I_E = 0\text{ A}$; $i_e = 0\text{ A}$; $f = 1\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	10	-	pF
C_e	emitter capacitance	$V_{EB} = -0.5\text{ V}$; $I_C = 0\text{ A}$; $i_c = 0\text{ A}$; $f = 1\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	150	-	pF



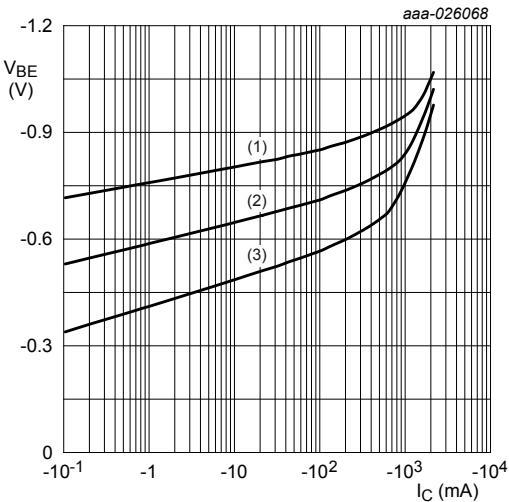
$V_{CE} = -10\text{ V}$
(1) $T_{amb} = 100^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = -55^\circ\text{C}$

Fig. 3. DC current gain as a function of collector current; typical values



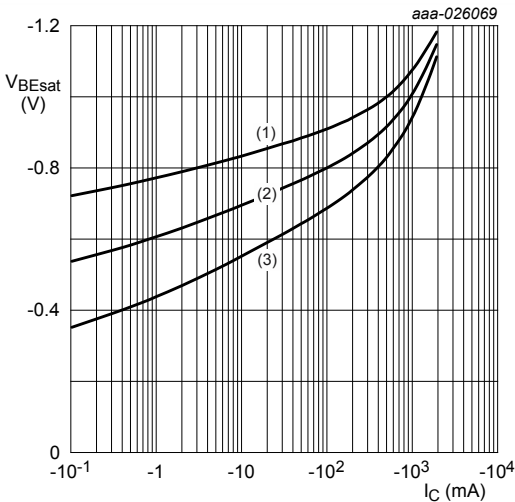
$T_{amb} = 25^\circ\text{C}$

Fig. 4. Collector current as a function of collector-emitter voltage; typical values



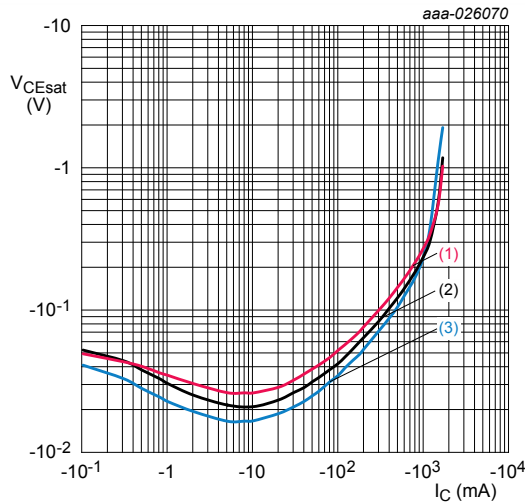
$V_{CE} = -10\text{ V}$
(1) $T_{amb} = -55^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = 100^\circ\text{C}$

Fig. 5. Base-emitter voltage as a function of collector current; typical values



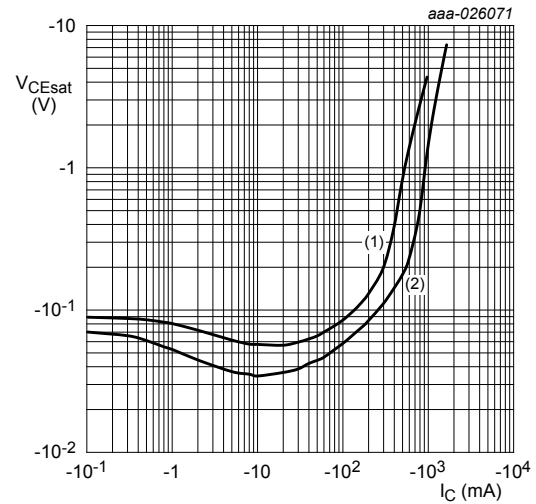
$I_C/I_B = 5$
(1) $T_{amb} = -55^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = 100^\circ\text{C}$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values



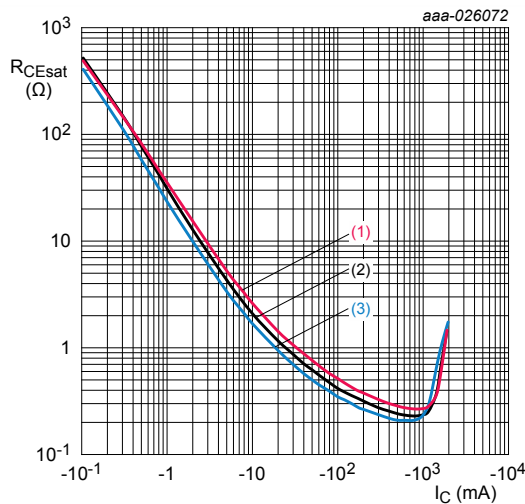
$I_C/I_B = 5$
 (1) $T_{amb} = 100^\circ\text{C}$
 (2) $T_{amb} = 25^\circ\text{C}$
 (3) $T_{amb} = -55^\circ\text{C}$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



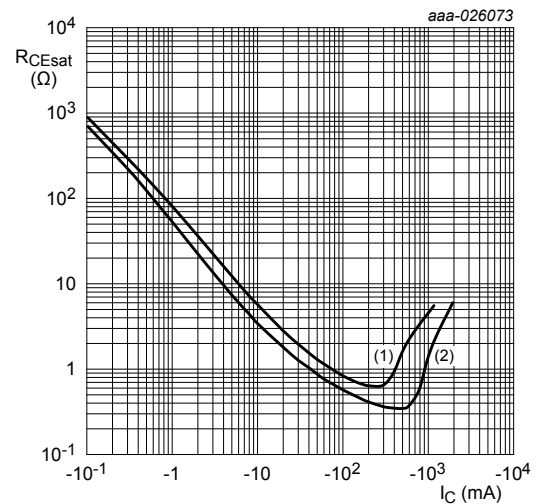
$T_{amb} = 25^\circ\text{C}$
 (1) $I_C/I_B = 20$
 (2) $I_C/I_B = 10$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 5$
 (1) $T_{amb} = 100^\circ\text{C}$
 (2) $T_{amb} = 25^\circ\text{C}$
 (3) $T_{amb} = -55^\circ\text{C}$

Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25^\circ\text{C}$
 (1) $I_C/I_B = 20$
 (2) $I_C/I_B = 10$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

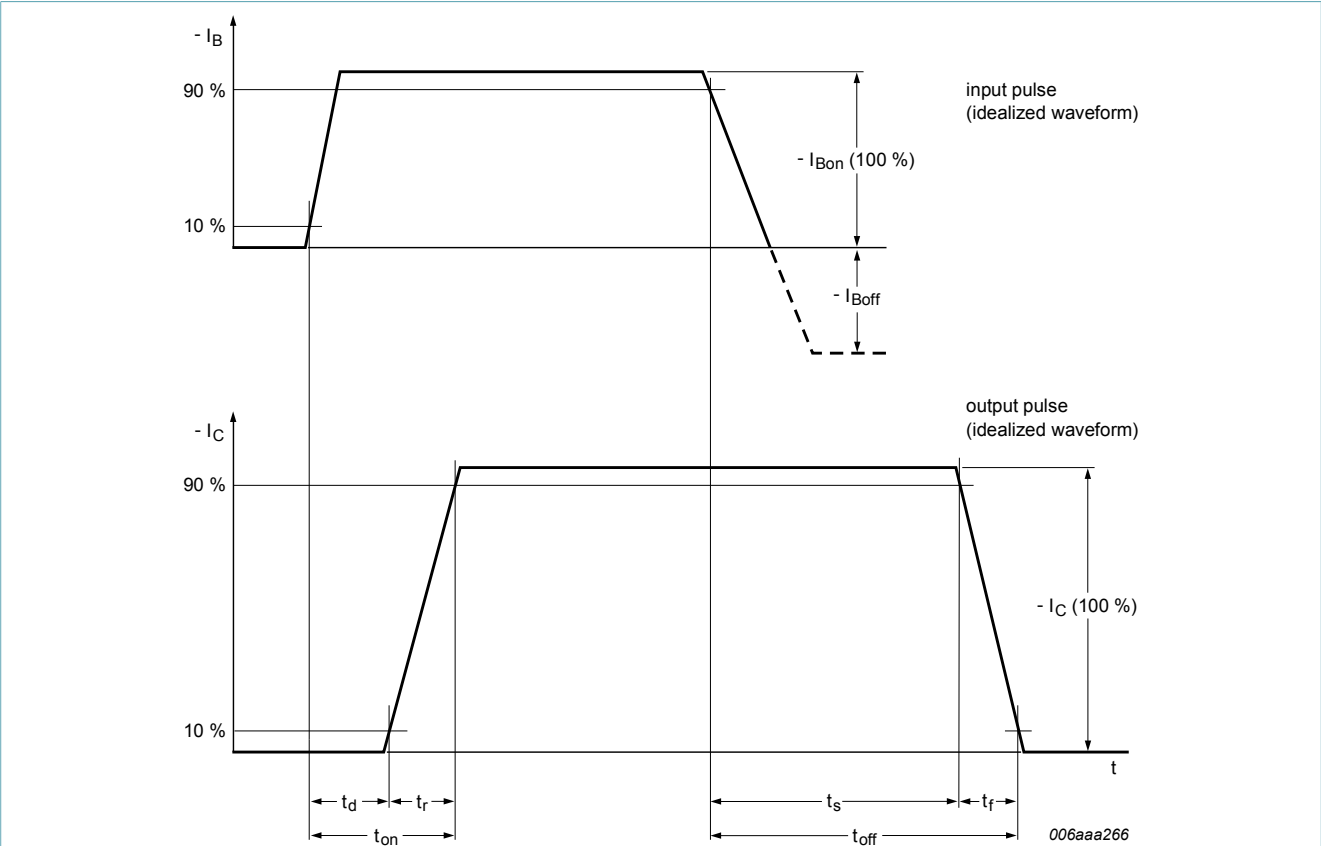


Fig. 11. BISS transistor switching time definition

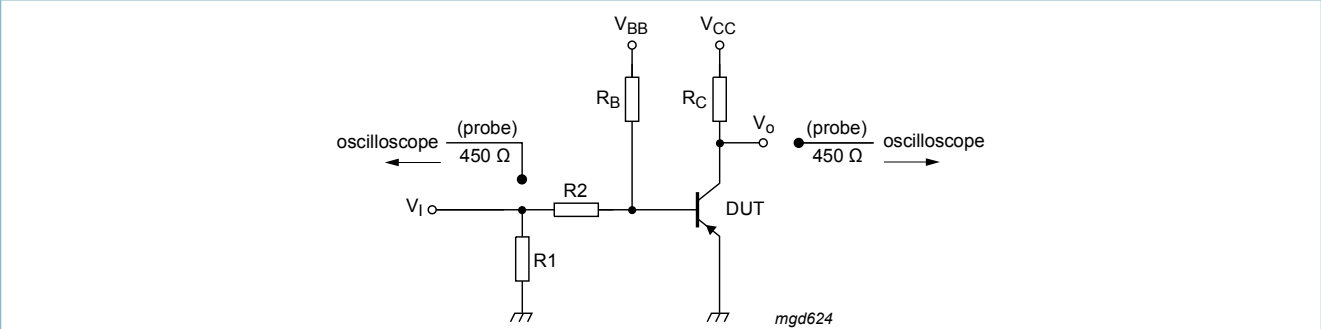
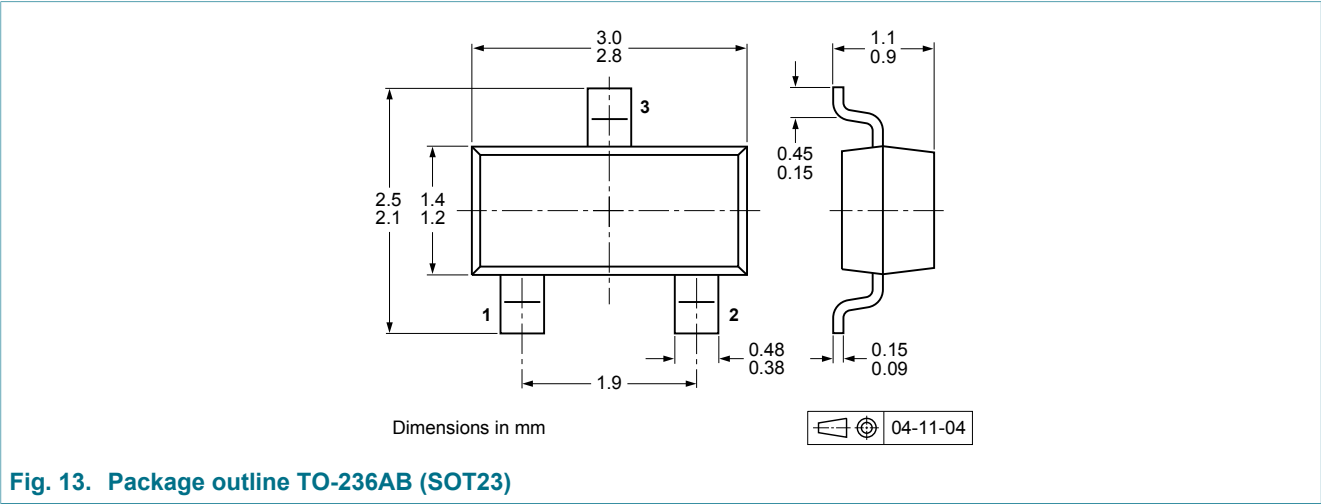


Fig. 12. Test circuit for switching times

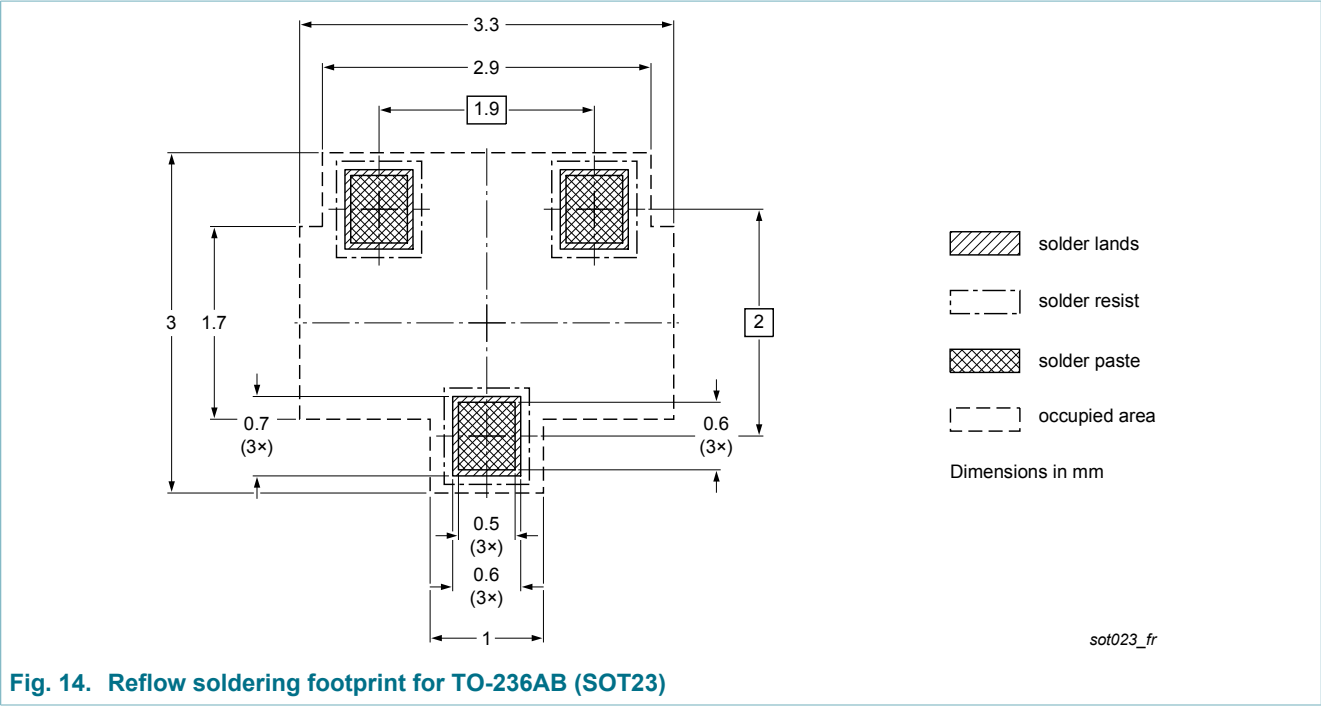
Quality information

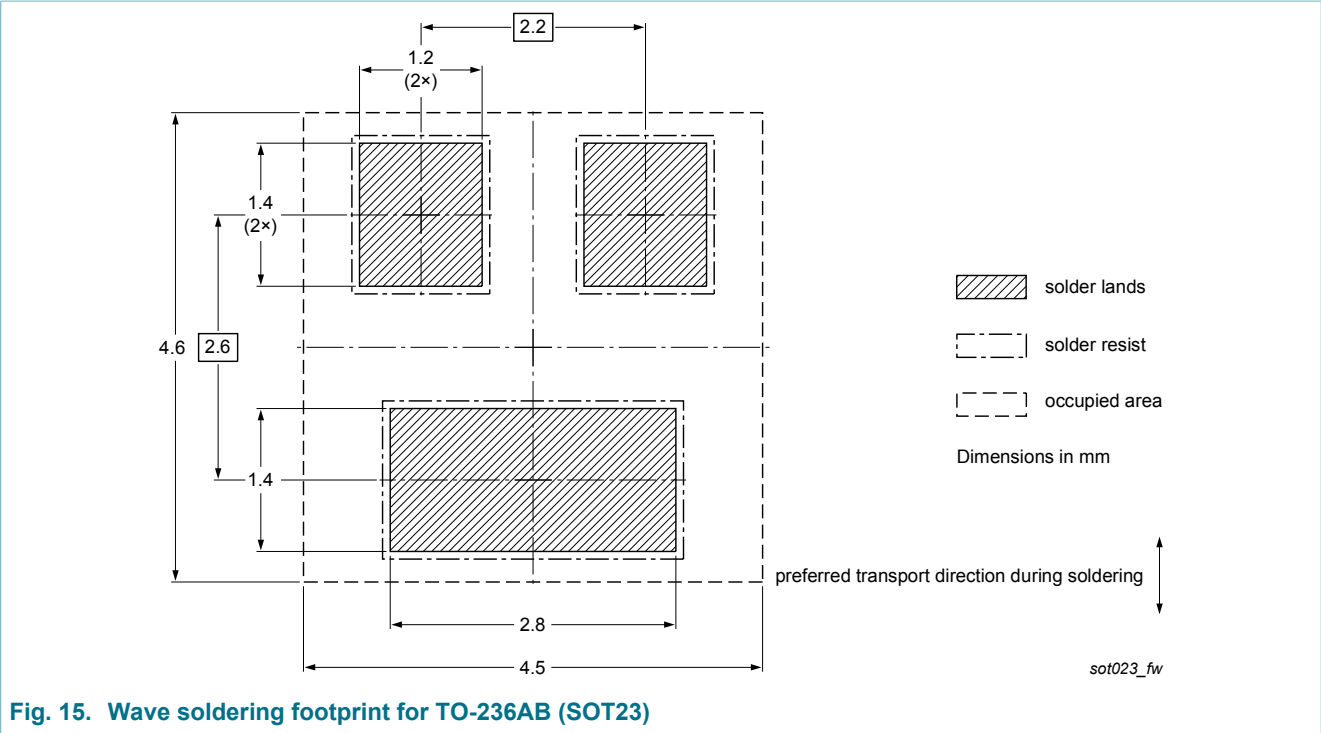
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



13. Soldering





14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9115TLH v.1	20170116	Product data sheet	-	-

15. Legal information

Data sheet status

Document status ^{[1] [2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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16. Contents

1. General description.....	1
2. Features and benefits.....	1
3. Applications.....	1
4. Quick reference data.....	1
5. Pinning information.....	2
6. Ordering information.....	2
7. Marking.....	2
8. Limiting values.....	3
9. Thermal characteristics.....	4
10. Characteristics.....	5
11. Test information.....	8
12. Package outline.....	9
13. Soldering.....	9
14. Revision history.....	11
15. Legal information.....	12

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